Composite Transistors

Panasonic

XP01878

Silicon N-channel MOSFET

For switching

Features

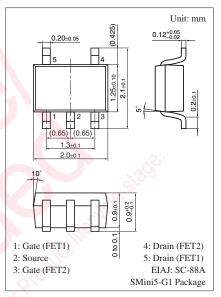
- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

• 2SK3539 × 2

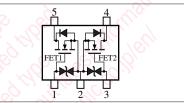
Absolute Maximum Ratings $T_a = 25^{\circ}C$

| 0 | u | | |
|----------------------------------|------------------|-------------|------|
| Parameter | Symbol | Rating | Unit |
| Drain-source surrender voltage | V _{DSS} | 50 | V |
| Gate-source voltage (Drain open) | V _{GSO} | ±7 | v |
| Drain current | ID | 100 | mA |
| Peak drain current | I _{DP} | 200 | mA |
| Total power dissipation | PT | 150 | mW |
| Channel temperature | T _{ch} | 150 | °C |
| Storage temperature | T _{stg} | -55 to +125 | °C |
| | | | |



Marking Symbol: AL

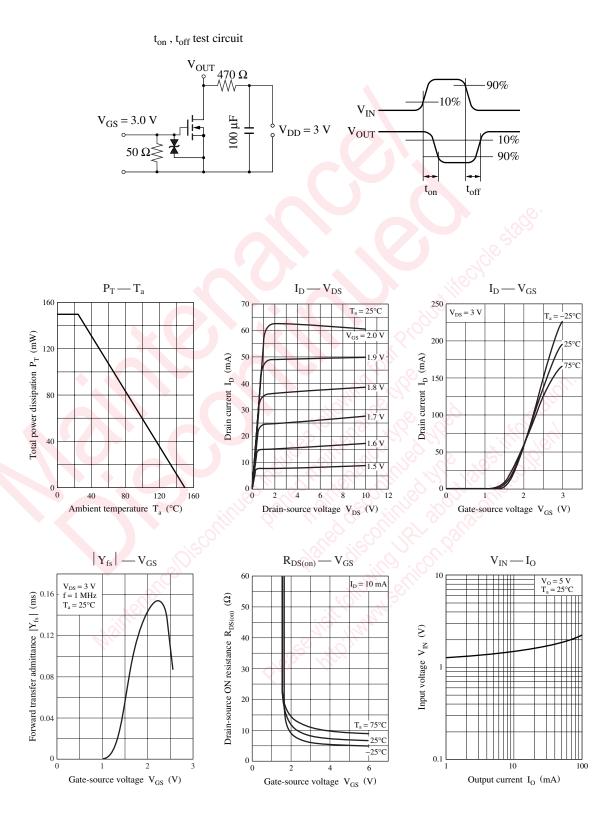
Internal Connection



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|---------------------|--|-----|-----|-----|------|
| Drain-source surrender voltage | VDSS | $I_{\rm D} = 10 \ \mu A, \ V_{\rm GS} = 0$ | 50 | | | V |
| Drain-source cutoff current | I _{DSS} | $V_{DS} = 50 V, V_{GS} = 0$ | | | 1.0 | μΑ |
| Gate-source cutoff current | I _{GSS} | $V_{GS} = \pm 7 V, V_{DS} = 0$ | | | ±5 | μΑ |
| Gate threshold voltage | V _{th} | $I_D = 1 \ \mu A, \ V_{DS} = 3 \ V$ | 0.9 | 1.2 | 1.5 | V |
| Drain-source ON resistance | R _{DS(on)} | $I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$ | | 8 | 15 | Ω |
| N.o. | | $I_D = 10 \text{ mA}, V_{GS} = 4.0 \text{ V}$ | | 6 | 12 | |
| Forward transfer admittance | Y _{fs} | $I_D = 10 \text{ mA}, V_{DS} = 4.0 \text{ V}$ | 20 | 60 | | mS |
| Short-circuit forward transfer capacitance (Common source) | C _{iss} | $V_{DS} = 3 V, V_{GS} = 0 V, f = 1 MHz$ | | 12 | | pF |
| Short-circuit output capacitance (Common source) | C _{oss} | | | 7 | | pF |
| Reverse transfer capacitance (Common source) | C _{rss} | | | 3 | | pF |
| Turn-on time * | t _{on} | V_{DD} = 3 V, V_{GS} = 0 V to 3 V, R_L = 470 Ω | | 200 | | ns |
| Turn-off time * | t _{off} | $V_{DD} = 3 V, V_{GS} = 3 V \text{ to } 0 V, R_L = 470 \Omega$ | | 200 | | ns |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Refer to t_{on} , t_{off} test circuit (next page)



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